Form PTO-1449 Modified List of Patents and Publications Cited by Applicant (Use several sheets if necessary) U.S. Patent Department of Commerce Patent and Trademark Office	Docket No.: 20661-801D1	Serial No.: 09/964,192
	Applicants: Varun Singh, et al.	COPY OF PAPERS ORIGINALLY FILED
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U.S. PATENT DOCUMENTS

Examiner Initial		Document No.	Date	Name	Class	Subclass
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EL	A-2	5,187,559	2/16/1993	Isobe et al.	257	538
EL	A-3	5,854,103	12/29/1998	Liang	438	238
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FOREIGN PATENT DOCUMENTS

Examiner Initial		Document No.	Date	Country	Translation	
					Yes	No
	B-1					

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OTHER DOCUMENTS

Examiner Initials		Author, Title, Date, Pertinent Pages, Etc.
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	C-5	"ElectricalTrimming of Ion-Beam-Sputtered Polysilicon Resistors by High Current Pulses", by Soumen Das and Samir K. Lahiri, IEEE Transactions on Electron Devices, Vol. 41, No. 8, August 1994
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	C-9	"Change in Temperature Coefficient of Resistance of Heavily Doped Polysilicon Resistors Caused by Electrical Trimming", by Kotaro Kato and Terukazu Ono, Jpn. J. Appl. Phys. Vol. 35, pp. 4209-4215, August 1996
	C-10	"Polycrystalline Silicon for Integrated Circuits and Displays Second Edition", by Ted Kamins, P. 266, 1998

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Date Examined: 6/12/02	**Examiner:**